

自主封測 品質把控 售後保障

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電源管理



顯示驅動



二三極管



LDO穩壓器



觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

AD7705-TD

產品規格說明書

AO340-TD

-30V, 48mΩ, -4.2A, Single P-Channel

1.Features

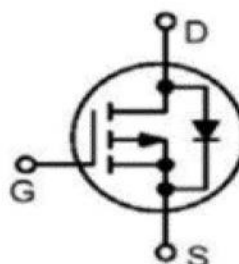
- ♦ High power and current handing capability
- ♦ Surface mount package

2.Applications

- ♦ Power Management
- ♦ Load Switching



V_{DS}	$R_{DS(on)}$ Max.	I_D
-30V	55mΩ @ -10V	-4.2A
	75mΩ @ -4.5V	
	90mΩ @ -2.5V	



3.Absolute Max Ratings at $T_a=25^{\circ}\text{C}$ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	-30	V
Gate to Source Voltage	V_{GSS}	± 12	V
Drain Current (DC)	I_D	-4.2	A
Drain Current (Pulse), $PW \leq 300\mu s$	I_{DP}	-30	A
Total Dissipation	P_D	1.2	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

4.Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction- to- Ambient	$R_{\theta JA}$	104	$^{\circ}\text{C}/\text{W}$

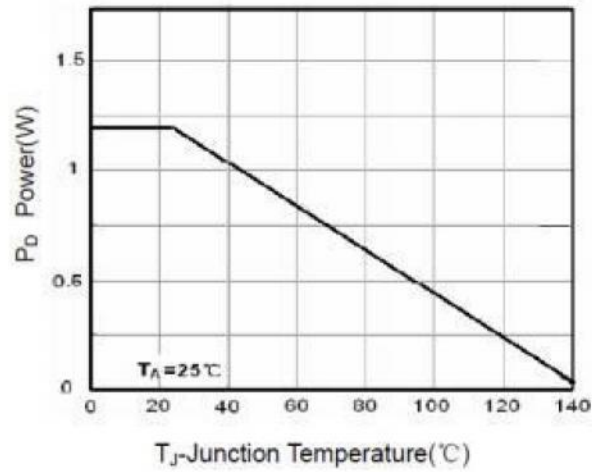
Note 2 : When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

5. Electrical Characteristics at Ta=25°C (Note 3)

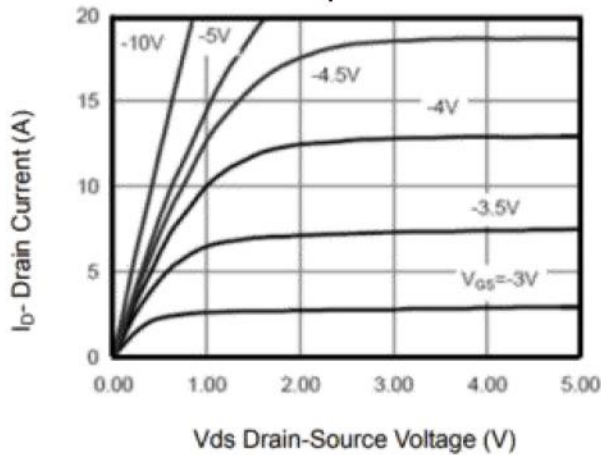
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -250\mu A, V_{GS} = 0V$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{DS} = -250\mu A$	-0.7	-1	1.3	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = -4.2A, V_{GS} = -10V$		48	55	m Ω
		$I_D = -4A, V_{GS} = -4.5V$		56	75	m Ω
		$I_D = -1A, V_{GS} = -2.5V$		72	90	m Ω
Forward Transconductance	g_{fs}	$V_{DS} = -5V, I_D = -4.2A$		10		S
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = -15V,$ Frequency=1.0MHz		880		pF
Output Capacitance	C_{oss}			105		pF
Reverse Transfer Capacitance	C_{rss}			65		pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DS} = -15V, I_D = -4.2A,$ $V_{GS} = -10V, R_{GEN} = 6\Omega$		7		ns
Rise Time	t_r			3		ns
Turn-OFF Delay Time	$t_{d(off)}$			30		ns
Fall Time	t_f			12		ns
Total Gate Charge	Q_g	$V_{DS} = -15V,$		8.5		nC
	Q_{gs}	$V_{GS} = -4.5V,$		1.8		nC
	Q_{gd}	$I_D = -4.2A$		2.7		nC
Diode Forward Voltage	V_{FSD}	$I_S = -4.2A, V_{GS} = 0$			-1.2	V

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

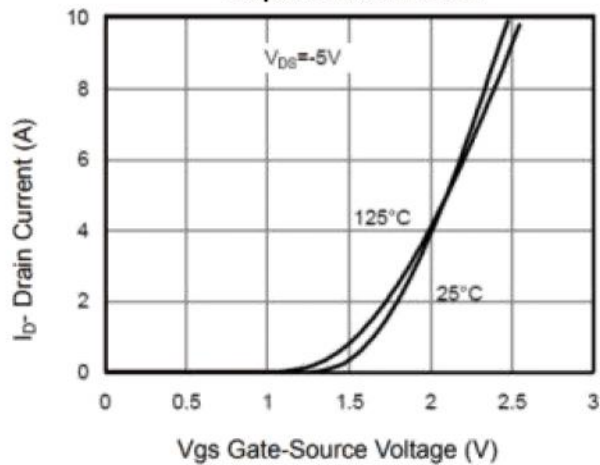
6. Typical Electrical and Thermal Characteristics



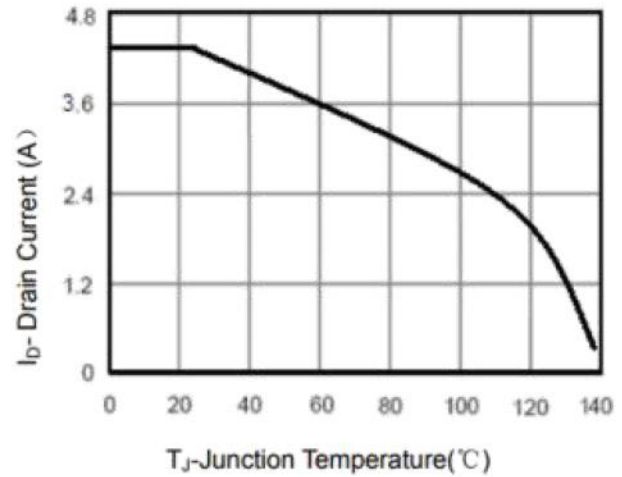
Power Dissipation



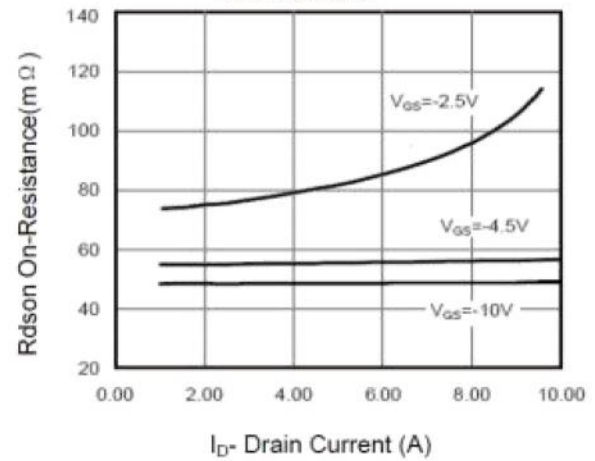
Output Characteristics



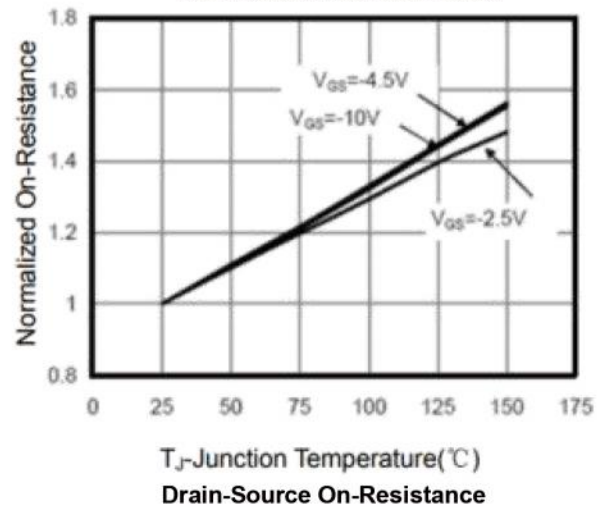
Transfer Characteristics



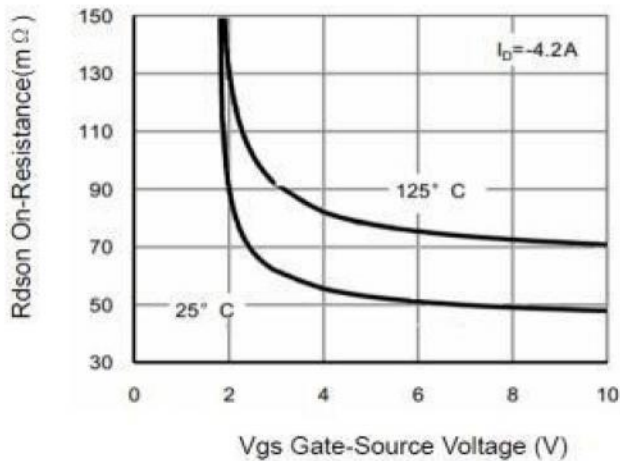
Drain Current



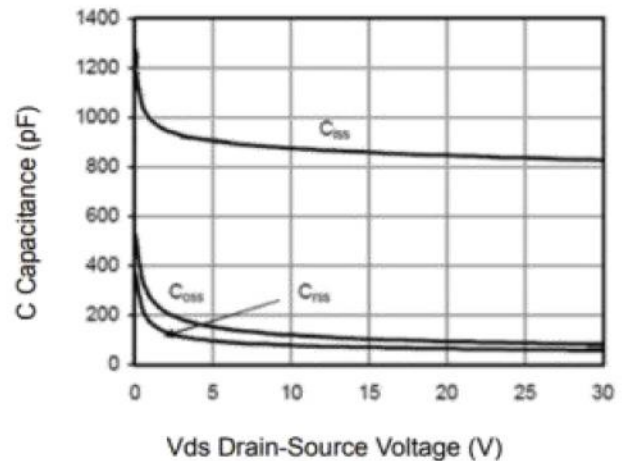
Drain-Source On-Resistance



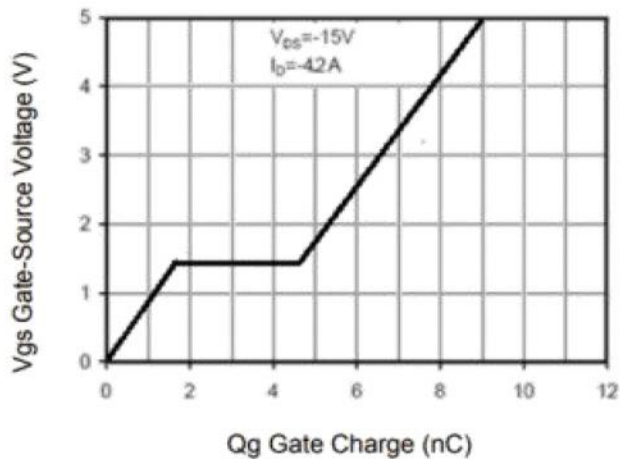
AO3401-TD



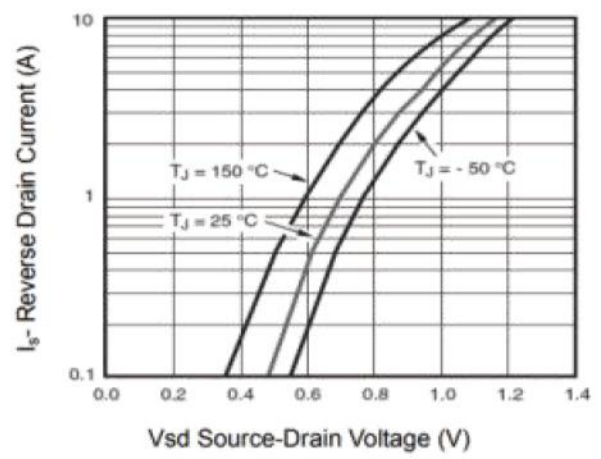
Rdson vs. Vgs



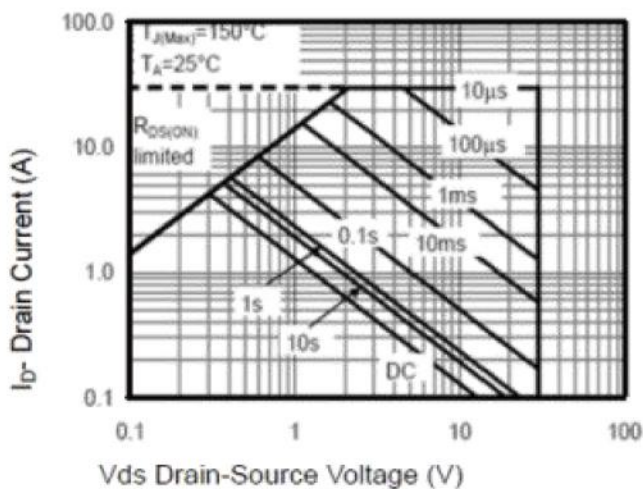
Capacitance vs. Vds



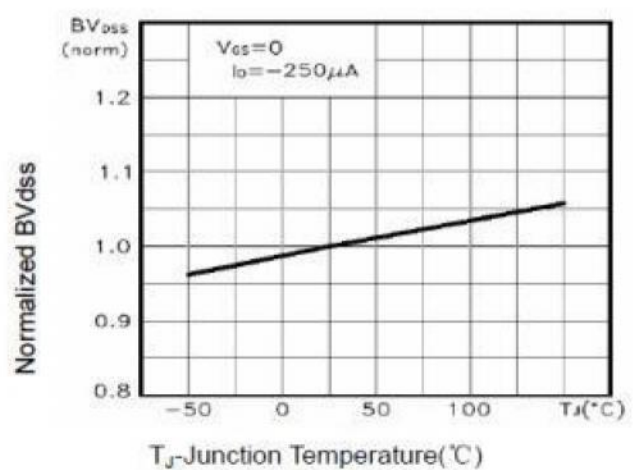
Gate Charge



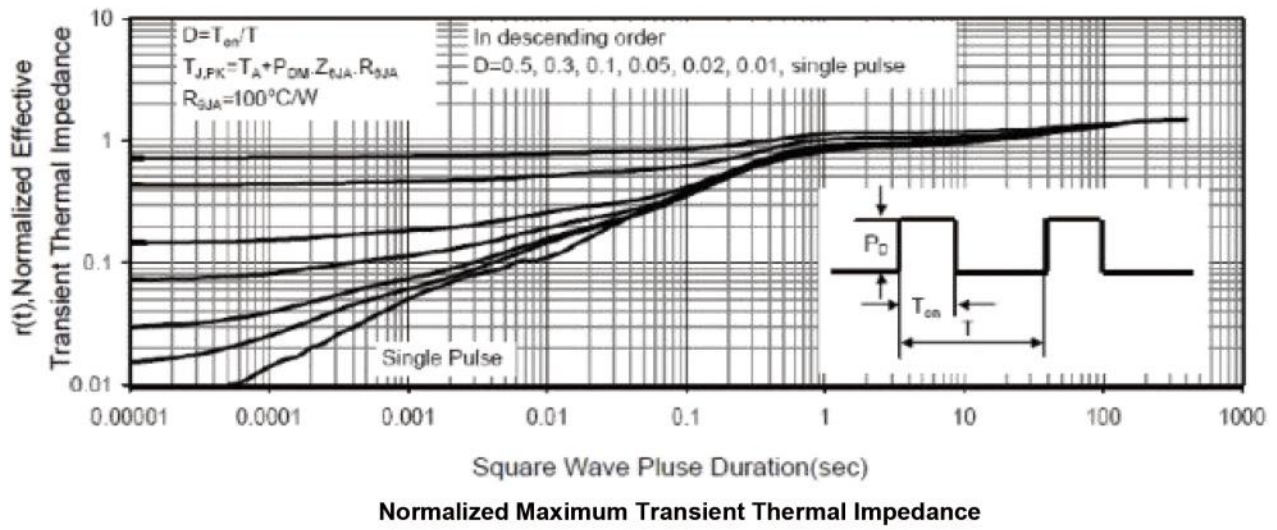
Source- Drain Diode Forward



Safe Operation Area



BVdss vs. Junction Temperature



7.Package Dimensions

